

L Number	Hits	Search Text	DB	Time stamp
2	18	117/\$4.ccls. and indium same flux and ("as.sub.4" or "as.sub.2" or arsenic) same flux	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 09:45
3	25	117/\$4.ccls. and inas same ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 09:55
8	30	indium same cell same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 10:20
12	51	(inas same substrate same temperature) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 11:19
16	22	evaporation same temperature same rate same gaas and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 11:44
-	46	117/\$4.ccls. and gaas and native adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 13:53
-	19	117/\$4.ccls. and gaas and (desorp\$4 same (arsenic or "as.sub.2" or "as.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:03
-	187	117/\$4.ccls. and super\$1lattice and (gaas same substrate) and @py:2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:32
-	40	117/\$4.ccls. and super\$1lattice and (gaas same substrate) and @py:2001 and inas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:35
-	25	117/\$4.ccls. and super\$1lattice and (gaas same substrate) and @py:2001 and inas and mbe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:38
-	60	(gaas same substrate) and inas and buffer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 15:41
-	83	(arsenic or "as.sub.2" or "as.sub.4") and adjust\$3 same thickness and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 10:23
-	48	(arsenic or "as.sub.2" or "as.sub.4") and adjust\$3 same thickness same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 10:29

-	150	117/\$4.ccls. and amorphous and anneal\$3 and gaas	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 10:30
-	63	117/\$4.ccls. and amorphous same anneal\$3 and gaas	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 10:32
-	54	117/\$4.ccls. and (ga or gallium) same cell same temperature and mbe	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 13:22
-	44	117/\$4.ccls. and gaas same buffer and inas	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 13:29
-	12	117/\$4.ccls. and evaporate same temperature same arsenic	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 13:50
-	63	117/\$4.ccls. and evaporat\$3 same temperature same arsenic	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 13:50
-	186	117/\$4.ccls. and single adj crystal same amorphous and gaas	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 15:31
-	57	117/\$4.ccls. and single adj crystal same amorphous same gaas	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 16:11
-	190	117/\$4.ccls. and low adj temperature same gaas	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 16:17
-	30	117/\$4.ccls. and low adj temperature same gaas same pressure	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/19 16:14
-	165	117/\$4.ccls. and gaas same pressure and mbe	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/07/22 09:39